



FAST CMOS BUFFER CLOCK/DRIVER

IDT49FCT805/A

FEATURES:

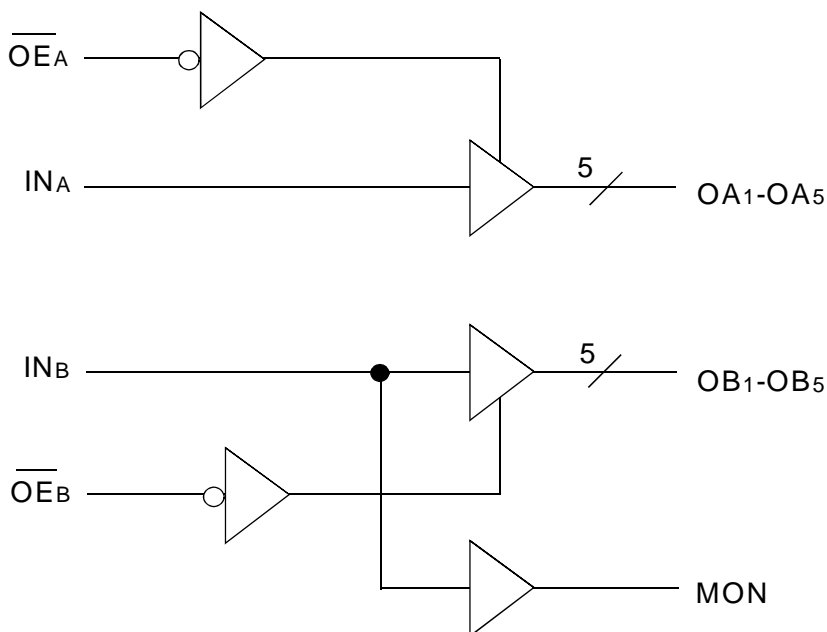
- 0.5 MICRON CMOS Technology
- Guaranteed low skew < 700ps (max.)
- Low duty cycle distortion < 1ns (max.)
- Low CMOS power levels
- TTL compatible inputs and outputs
- Rail-to-rail output voltage swing
- High drive: -24mA IOH, +64mA IOL
- Two independent output banks with 3-state control
- 1:5 fanout per bank
- "Heartbeat" monitor output
- Available in SOIC and SSOP packages

DESCRIPTION:

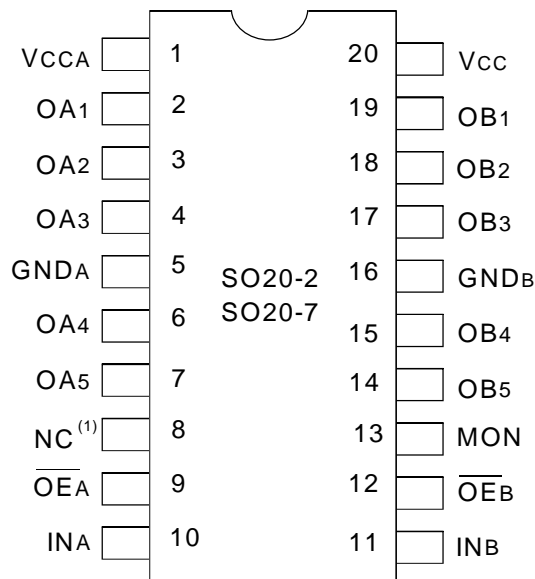
The 49FCT805 is a non-inverting buffer/clock driver built using advanced dual metal CMOS technology. Each bank consists of two banks of drivers. Each bank drives five output buffers from a standard TTL compatible input. These devices feature a "heart-beat" monitor for diagnostics and PLL driving. The MON output is identical to all other outputs and complies with the output specifications in this document.

The 49FCT805 offers low capacitance inputs and hysteresis. Rail-to-rail output swing improves noise margin and allows easy interface with CMOS inputs.

FUNCTIONAL BLOCK DIAGRAM



PIN CONFIGURATION



SOIC/ SSOP
TOP VIEW

NOTE:

1. Pin 8 is not internally connected on devices with a "K" prefix in the date code. On older devices, pin 8 is internally connected to GND. To insure compatibility with all products, pin 8 should be connected to GND at the board level.

ABSOLUTE MAXIMUM RATINGS⁽¹⁾

Symbol	Rating	Max.	Unit
V _{TERM} ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +7	V
V _{TERM} ⁽³⁾	Terminal Voltage with Respect to GND	-0.5 to V _{CC} +0.5	V
T _{STG}	Storage Temperature	-65 to +150	°C
I _{OUT}	DC Output Current	-60 to +120	mA

NOTE:

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability. No terminal voltage may exceed V_{CC} by +0.5V unless otherwise noted.
- Input and V_{CC} terminals.
- Output and I/O terminals.

CAPACITANCE (T_A = +25°C, f = 1.0MHz)

Symbol	Parameter ⁽¹⁾	Conditions	Typ.	Max.	Unit
C _{IN}	Input Capacitance	V _{IN} = 0V	4.5	6	pF
C _{OUT}	Output Capacitance	V _{OUT} = 0V	5.5	8	pF

NOTE:

- This parameter is measured at characterization but not tested.

PIN DESCRIPTION

Pin Names	Description
$\overline{OE_A}$, $\overline{OE_B}$	3-State Output Enable Inputs (Active LOW)
INA, INB	Clock Inputs
OAn, OBn	Clock Outputs
MON	Monitor Output

FUNCTION TABLE⁽¹⁾

Inputs		Outputs	
$\overline{OE_A}$, $\overline{OE_B}$	INA, INB	OAn, OBn	MON
L	L	L	L
L	H	H	H
H	L	Z	L
H	H	Z	H

NOTE:

- H = HIGH Voltage Level
L = LOW Voltage Level
Z = High-Impedance

DC ELECTRICAL CHARACTERISTICS OVER OPERATING RANGE

Following Conditions Apply Unless Otherwise Specified: $V_{LC} = 0.2V$; $V_{HC} = V_{CC} - 0.2V$

Commercial: $T_A = 0^{\circ}C$ to $+70^{\circ}C$, Industrial: $T_A = -40^{\circ}C$ to $+85^{\circ}C$, $V_{CC} = 5.0V \pm 5\%$

Symbol	Parameter	Test Conditions ⁽¹⁾		Min.	Typ. ⁽²⁾	Max.	Unit
V_{IH}	Input HIGH Level	Guaranteed Logic HIGH Level		2	—	—	V
V_{IL}	Input LOW Level	Guaranteed Logic LOW Level		—	—	0.8	V
I_{IH}	Input HIGH Current	$V_{CC} = \text{Max.}$	$V_I = V_{CC}$	—	—	± 1	μA
I_{IL}	Input LOW Current	$V_{CC} = \text{Max.}$	$V_I = GND$	—	—	± 1	μA
I_{OZH}	Off State (HIGH Z) Output Current	$V_{CC} = \text{Max.}$	$V_O = V_{CC}$	—	—	± 1	μA
I_{OZL}			$V_O = GND$	—	—	± 1	
V_{IK}	Clamp Diode Voltage	$V_{CC} = \text{Min.}, I_{IN} = -18mA$		—	-0.7	-1.2	V
I_{OS}	Short Circuit Current	$V_{CC} = \text{Max.}^{(3)}, V_O = GND$		-60	-120	—	mA
V_{OH}	Output HIGH Voltage	$V_{CC} = 3V, V_{IN} = V_{LC} \text{ or } V_{HC}, I_{OH} = -32\mu A$		V_{HC}	V_{CC}	—	V
		$V_{CC} = \text{Min.}$ $V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OH} = -300\mu A$	V_{HC}	V_{CC}	—	
			$I_{OH} = -15mA$	3.6	4.3	—	
			$I_{OH} = -24mA$	2.4	3.8	—	
V_{OL}	Output LOW Voltage	$V_{CC} = 3V, V_{IN} = V_{LC} \text{ or } V_{HC}, I_{OL} = 300\mu A$		—	GND	V_{LC}	V
		$V_{CC} = \text{Min.}$ $V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OL} = 300mA$	—	GND	V_{LC}	
			$I_{OL} = 64mA$	—	0.3	0.55	
V_H	Input Hysteresis for all inputs	—		—	200	—	mV
I_{CC}	Quiescent Power Supply Current	$V_{CC} = \text{Max.}, V_{IN} = GND \text{ or } V_{CC}$		—	5	500	μA

NOTES:

1. For conditions shown as max. or min., use appropriate value specified under Electrical Characteristics for the applicable device type.
2. Typical values are at $V_{CC} = 5.0V$, $+25^{\circ}C$ ambient.
3. Not more than one output should be shorted at one time. Duration of the short circuit test should not exceed one second.

POWER SUPPLY CHARACTERISTICS

Symbol	Parameter	Test Conditions ⁽¹⁾		Min.	Typ. ⁽²⁾	Max.	Unit
ΔI_{CC}	Quiescent Power Supply Current TTL Inputs HIGH	$V_{CC} = \text{Max.}$ $V_{IN} = 3.4V^{(3)}$		—	1	2.5	mA
I_{CCD}	Dynamic Power Supply Current ⁽⁴⁾	$V_{CC} = \text{Max.}$ Outputs Open $\overline{OE}_A = \overline{OE}_B = \text{GND}$ 50% Duty Cycle	$V_{IN} = V_{CC}$ $V_{IN} = \text{GND}$	—	0.15	0.2	mA/ MHz/bit
I_C	Total Power Supply Current ⁽⁶⁾	$V_{CC} = \text{Max.}$ Outputs Open $f_o = 10\text{MHz}$ 50% Duty Cycle $\overline{OE}_A = \overline{OE}_B = V_{CC}$ Mon. Output Toggling	$V_{IN} = V_{CC}$ $V_{IN} = \text{GND}$	—	1.5	2.5	mA
			$V_{IN} = 3.4V$ $V_{IN} = \text{GND}$	—	2	3.8	
		$V_{CC} = \text{Max.}$ Outputs Open $f_o = 2.5\text{MHz}$ 50% Duty Cycle $\overline{OE}_A = \overline{OE}_B = \text{GND}$ Eleven Outputs Toggling	$V_{IN} = V_{CC}$ $V_{IN} = \text{GND}$	—	4.1	6 ⁽⁵⁾	
			$V_{IN} = 3.4V$ $V_{IN} = \text{GND}$	—	5.1	8.5 ⁽⁵⁾	

NOTES:

- For conditions shown as Max. or Min., use appropriate value specified under Electrical Characteristics for the applicable device type.
- Typical values are at $V_{CC} = 5.0V$, $+25^\circ\text{C}$ ambient.
- Per TTL driven input ($V_{IN} = 3.4V$). All other inputs at V_{CC} or GND .
- This parameter is not directly testable, but is derived for use in Total Power Supply Calculations.
- Values for these conditions are examples of the I_{CC} formula. These limits are guaranteed but not tested.
- $I_C = I_{\text{QUIESCENT}} + I_{\text{INPUTS}} + I_{\text{DYNAMIC}}$
 $I_C = I_{CC} + \Delta I_{CC} D_H N_T + I_{CCD} (f_o N_o)$
 $I_{CC} = \text{Quiescent Current } (I_{CCL}, I_{CCH}, \text{ and } I_{CCZ})$
 $\Delta I_{CC} = \text{Power Supply Current for a TTL High Input } (V_{IN} = 3.4V)$
 $D_H = \text{Duty Cycle for TTL Inputs High}$
 $N_T = \text{Number of TTL Inputs at } D_H$
 $I_{CCD} = \text{Dynamic Current Caused by an Input Transition Pair (HLH or LHL)}$
 $f_o = \text{Output Frequency}$
 $N_o = \text{Number of Outputs at } f_o$
 All currents are in milliamps and all frequencies are in megahertz.

SWITCHING CHARACTERISTICS OVER OPERATING RANGE (1)

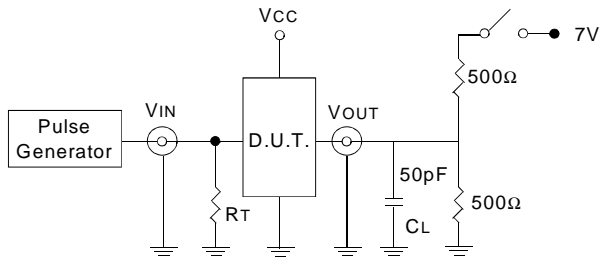
Symbol	Parameter	Condition ⁽²⁾	FCT805		FCT805A		Unit
			Min.	Max.	Min.	Max.	
t _{PLH} t _{PHL}	Propagation Delay I _{NA} to O _{AN} , I _{NB} to O _{BN}	C _L = 50pF R _L = 500Ω	1.5	5.6	1.5	5.3	ns
t _R	Output Rise Time		—	1.5	—	1.5	ns
t _F	Output Fall Time		—	1.5	—	1.5	ns
tsk(o)	Output skew: skew between outputs of all banks of same package (inputs tied together)		—	0.7	—	0.7	ns
tsk(p)	Pulse skew: skew between opposite transitions of same output (t _{PHL} – t _{PLH})		—	1	—	1	ns
tsk(pp)	Part-to-part skew: skew between outputs of different packages at same power supply voltage, temperature, package type and speed grade		—	1.5	—	1.5	ns
t _{PZL} t _{PZH}	Output Enable Time \overline{OE}_A to O _{AN} , \overline{OE}_B to O _{BN}		1.5	8	1.5	8	ns
t _{PLZ} t _{PHZ}	Output Disable Time \overline{OE}_A to O _{AN} , \overline{OE}_B to O _{BN}		1.5	7	1.5	7	ns

NOTES:

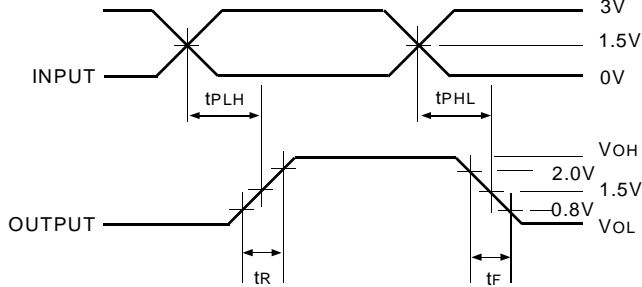
1. Propagation delay range indicated by Min. and Max. limit is due to V_{CC}, operating temperature, and process parameters. These propagation delay limits do not imply skew.
2. See Test Circuits and Waveforms.

TEST CIRCUITS AND WAVEFORMS

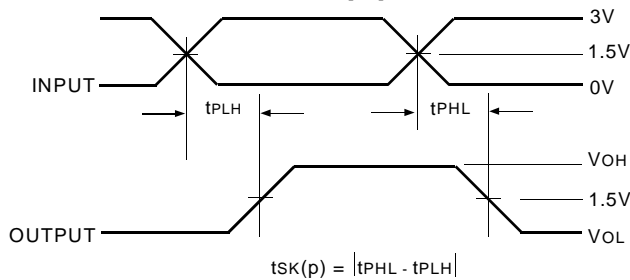
TEST CIRCUITS FOR ALL OUTPUTS



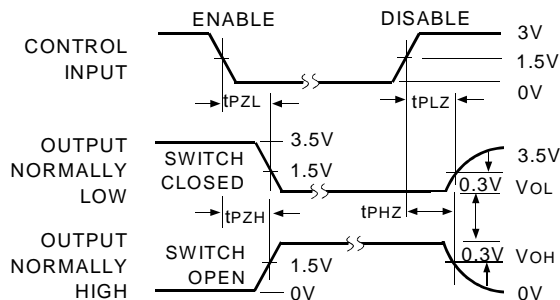
PACKAGE DELAY



PULSE SKEW - $t_{sk}(p)$



ENABLE AND DISABLE TIMES



NOTES:

- Diagram shown for input Control Enable-LOW and input Control Disable-HIGH
- Pulse Generator for All Pulses: Rate $\leq 1.0\text{MHz}$; $t_F \leq 2.5\text{ns}$; $t_R \leq 2.5\text{ns}$

ENABLE AND DISABLE TIMES SWITCH POSITION

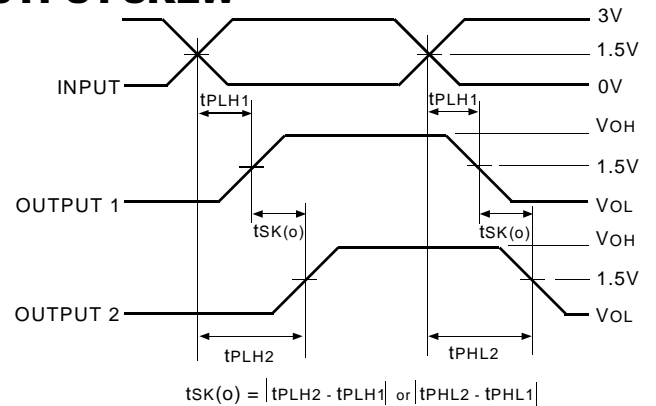
TEST	SWITCH
Disable LOW Enable LOW	Closed
Disable HIGH Enable HIGH	Open

DEFINITIONS:

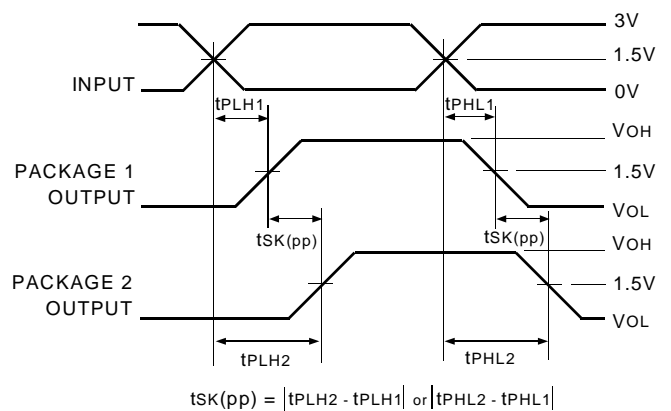
C_L = Load capacitance: includes jig and probe capacitance.

R_T = Termination resistance: should be equal to Z_{OUT} of the Pulse Generator.

OUTPUT SKEW



PART-TO-PART SKEW - $t_{sk}(pp)$



NOTE:

- Package 1 and Package 2 are same device type and speed grade.

ORDERING INFORMATION

IDT49FCT	XXXX	X	X		
	Device Type	Package	Process		
				Blank	Commercial (0°C to +70°C)
				I	Industrial (-40°C to +85°C)
				SO	Small Outline IC (SO20-2)
				PY	Shrink Small Outline Package (SO20-7)
				805	Fast CMOS Buffer/Clock Driver
				805A	



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